



Data sheet 2L10-B_SU7

Active area: 10 x 10 mm²
Chip area: 12,2 x 12,2 mm²

Characteristics	Min.	Typ.	Max.	Unit
Position non-linearity		0,3	0,8	% (±)
Detector resistance	7	10	16	kΩ
Leakage current		100	800	nA
Noise current		1,3	1,7	pA/√Hz
Responsivity		0,5		A/W
Capacitance		70	80	pF
Rise time (10%-90%)		350	600	ns
Bias voltage (reverse)	5	15	20	V
Thermal drift		40	200	ppm/°C

Maximum ratings

Reverse voltage			30	V
Operating temperature			70	°C
Storage temperature			100	°C

Test conditions: Room temperature 23 °C, bias voltage 15V, light source wavelength 1064 nm. Position non-linearity and thermal drift are valid within 80 % of the detector length.

Package: Ceramic substrate, 25,0 x 21,0 mm², with solderable pins and protective window.

Registration no.	Part no.	Written by:	Date.
S2-0017-D_A	S2-0017	Anders Lundgren	2003-05-13